a crystalline semiconductor film comprising a source region, a drain region, and a channel formation region formed between said source region and said drain region, the respective regions ~~begin~~ being in contact with said gate insulating film;

wherein said gate insulating film includes a layer of a silicon nitride oxide film containing boron.

2. (Previously amended) A semiconductor device according to claim 1, wherein a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

3. (Previously amended) A semiconductor device according to claim 1, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.

4. (Previously amended) A semiconductor device according to claim 1, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

5. (Previously amended) A semiconductor device according to claim 4, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device, and an image sensor.

6. (Previously amended) A semiconductor device according to claim 4, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a

portable information terminal.

7. (Currently amended) A semiconductor device comprising:

a source region, a drain region, and a channel formation region formed between said source region and said drain region, the respective regions being in contact with an insulating surface;

a gate insulating film comprising at least a single layer on said channel formation region; and

a gate electrode to be in contact with said gate insulating film;

wherein said gate insulating film includes a layer of a silicon nitride oxide film containing boron.

8. (Previously amended) A semiconductor device according to claim 7, wherein a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

9. (Previously amended) A semiconductor device according to claim 7, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms %.

10. (Currently amended) A semiconductor device according to claim 7, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

11. (Previously amended) A semiconductor device according to claim 10, wherein said

electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, and EC display device, and an image sensor.

12. (Currently amended) A semiconductor device according to claim 10, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.

13. (Currently amended) A semiconductor device comprising:

an insulating film formed on an insulating surface; and

a semiconductor component formed on said insulating film, said semiconductor component comprising crystalline semiconductor film as a channel formation region thereof;

wherein said insulating film is a silicon nitride oxide film containing boron.

14. (Currently amended) A semiconductor device according to claim 13, wherein a composition ~~ration~~ ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

15. (Previously amended) A semiconductor device according to claim 13, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.

16. (Previously amended) A semiconductor device according to claim 13, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

17. (Currently amended) A semiconductor ~~display~~ device according to claim 16, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device, and an image sensor.

18. (Currently amended) A semiconductor ~~display~~ device according to claim 16, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.

19. (Currently amended) A semiconductor device comprising:

a semiconductor component formed on an insulating surface; and

an insulating film for protecting said semiconductor component, said semiconductor component comprising crystalline semiconductor film as a channel formation region thereof;

wherein said insulating film is a silicon nitride oxide film containing boron.

20. (Currently amended) A semiconductor device according to claim 19, wherein a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

21. (Previously amended) A semiconductor device according to claim 19, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.

22. (Previously amended) A semiconductor device according to claim 19, wherein said

semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

23. (Previously amended) A semiconductor device according to claim 22, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device, and an image sensor.

24. (Previously amended) A semiconductor device according to claim 22, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.

25-31. (Canceled)